651 SN: 09/838,084

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Guo-Qiang Lo, et al.

Assignee: Integrated Device Technology, Inc.

Title: DIELECTRIC ANTI-REFLECTIVE COATING SURFACE

TREATMENT TO PREVENT DEFECT GENERATION IN

ASSOCIATED WET CLEAN

Serial No: 09/838,084

Group No.: 2823

Filed:

4/18/2001

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Box Non-Fee Amendment ASSISTANT COMMISSIONER FOR PATENTS Washington, D. C. 20231

RESPONSE TO FIRST OFFICE ACTION

Sir:

Applicants submit the following remarks and amendments in response to the Office Action dated October 22, 2002.

IN THE CLAIMS

Rewrite Claims 1 and 13 as follows.

1. (Amended) A method for preventing the formation of watermark defects in a semiconductor process, the method comprising:

patterning a silicon oxynitride layer; then
etching a trench in a semiconductor substrate
through the patterned silicon oxynitride layer; then
conditioning the patterned silicon oxynitride
layer, wherein no wet clean step is performed between
the etching of the trench and the conditioning of the
patterned silicon oxynitride layer; and then